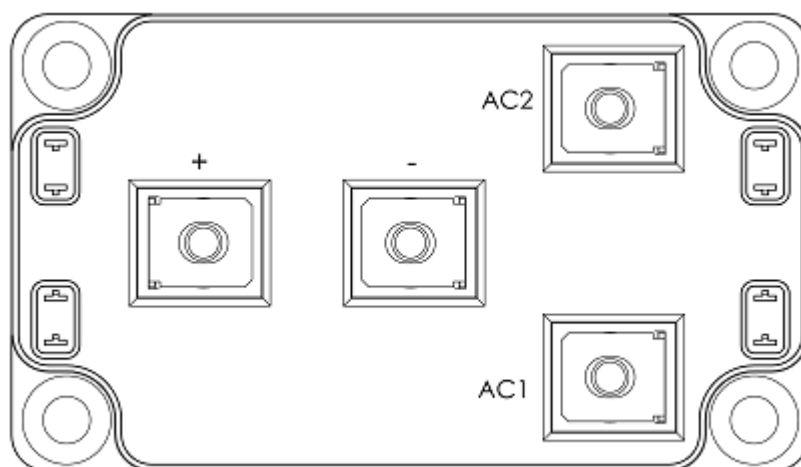
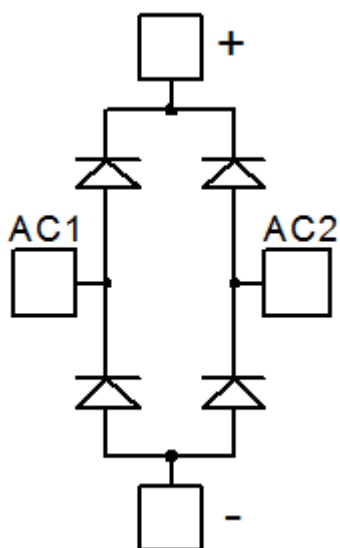


MSCDC100H70AG SiC Diode Full Bridge Power Module

1 Product Overview

This section shows the product overview of the MSCDC100H70AG device.



All ratings at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

1.1 Features

The following are key features of the MSCDC100H70AG device:

- Silicon carbide (SiC) Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- High blocking voltage
- Low stray inductance
- M5 power connectors
- Aluminum nitride (AlN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC100H70AG device:

- Outstanding performance at high-frequency operation
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC100H70AG device is designed for the following applications:

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

2 Electrical Specifications

This section shows the electrical specifications of the MSCDC100H70AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSCDC100H70AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage	700	V
I_F	DC forward current	$T_C = 70\text{ }^{\circ}\text{C}$ 100	A

The following table shows the thermal and package characteristics of the MSCDC100H70AG device.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit	
V _{ISOL}	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz	4000		V	
T _J	Operating junction temperature range	−40	175	°C	
T _{JOP}	Recommended junction temperature under switching conditions	−40	T _{Jmax} −25		
T _{STG}	Storage temperature range	−40	125		
T _C	Operating case temperature	−40	125		
Torque	Mounting torque	To heatsink	M6	3	N.m
		For terminals	M5	2	
Wt	Package weight			300	g

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC100H70AG device.

Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode forward voltage	$I_F = 100\text{ A}$ $T_J = 25\text{ }^{\circ}\text{C}$		1.5	1.8	V
				1.9		
I_{RM}	Reverse leakage current	$V_R = 700\text{ V}$ $T_J = 25\text{ }^{\circ}\text{C}$		30	400	μA
				500		
Q_C	Total capacitive charge	$V_R = 400\text{ V}$		266		nC
C	Total capacitance	$f = 1\text{ MHz}$, $V_R = 200\text{ V}$		496		pF
		$f = 1\text{ MHz}$, $V_R = 400\text{ V}$		432		
R_{thJC}	Junction-to-case thermal resistance				0.456	$^{\circ}\text{C/W}$

2.3 Typical Performance Curves

This section shows the typical performance curves of the MSCDC100H70AG device.

Figure 1 • Maximum Transient Thermal Impedance

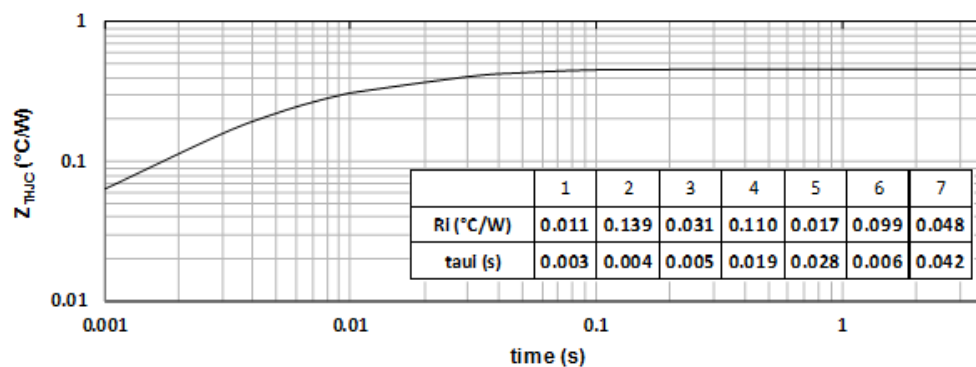


Figure 2 • Forward Current vs. Forward Voltage

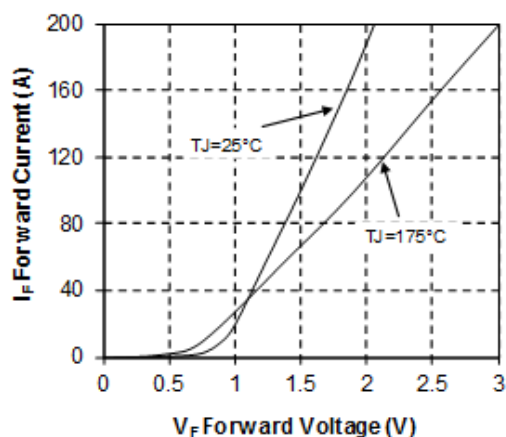
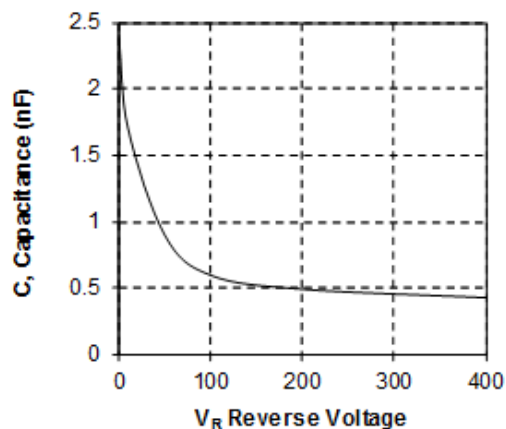


Figure 3 • Capacitance vs. Reverse Voltage



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MSCC-0344-DS-01025-1.0-0619 | June 2019 | Final